

PHP30NQ15T

N-channel TrenchMOS standard level FET Rev. 03 — 3 March 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC convertors

Switched-mode power supplies

1.4 Quick reference data

Table 1. **Quick reference**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	150	V
I_D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see <u>Figure 1</u> and <u>2</u>	-	-	29	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 3</u>	-	-	150	W
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A};$ $V_{DS} = 120 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13	-	20	27	nC
Static ch	naracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 11 and 12	-	60	63	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow \overline{A}$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP30NQ15T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	150	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	150	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{ and } 2}$	-	29	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	20	Α
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 2	-	116	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 3</u>	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
Is	source current	$T_{mb} = 25 ^{\circ}C$	-	29	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	116	Α
Avalanche	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 26 A; $V_{sup} \le$ 25 V; unclamped; R_{GS} = 50 Ω ; t_p = 0.2 ms; see <u>Figure 4</u>	-	502	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{ unclamped}; \text{ see } \frac{\text{Figure 4}}{\text{Figure 4}}$	-	29	Α

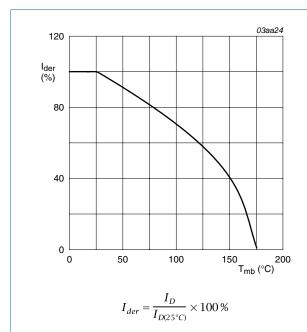
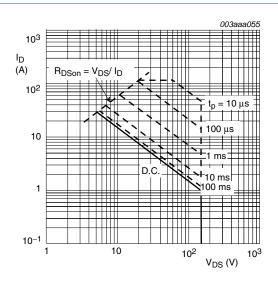


Fig 1. Normalized continuous drain current as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

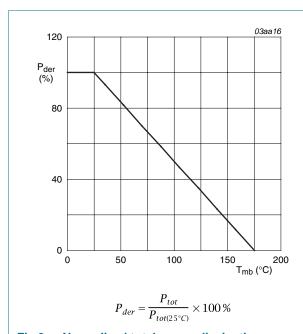
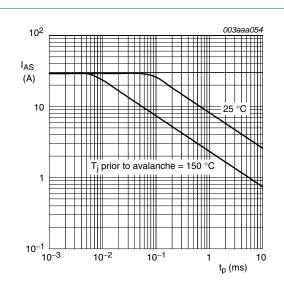


Fig 3. Normalized total power dissipation as a function of mounting base temperature



Unclamped inductive load; $V_{DS} \le 25V$; $R_{GS} = 50 \,\Omega$; $V_{GS} = 10V$; starting at $T_j = 25 \,^{\circ}C$ and $150 \,^{\circ}C$.

Fig 4. Non-repetitive avalanche ruggedness current as a function of pulse duration

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

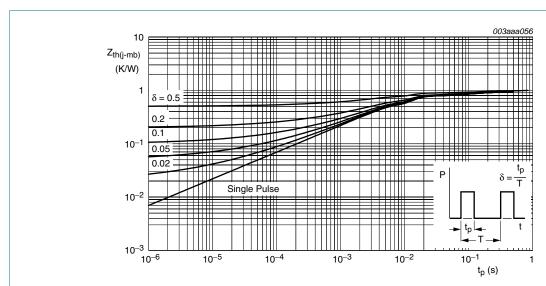


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	150	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 8	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 8	1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 150 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 150 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 11 and 12	-	-	176	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11 and 12	-	60	63	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 30 \text{ A}$; $V_{DS} = 120 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	55	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u>	-	10	-	nC
Q_{GD}	gate-drain charge		-	20	27	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2390	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$; see Figure 14	-	240	-	pF
C _{rss}	reverse transfer capacitance		-	98	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 75 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}C$	-	50	-	ns
$t_{d(off)}$	turn-off delay time		-	48	-	ns
t _f	fall time		-	38	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 15</u>	-	0.9	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	105	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	0.55	-	μC

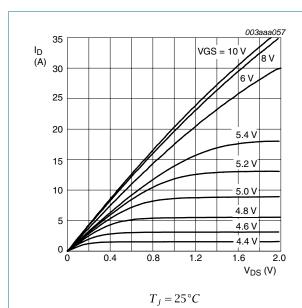


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

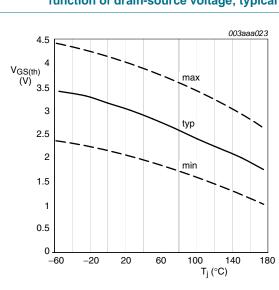


Fig 8. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1mA; V_{DS} = V_{GS}$

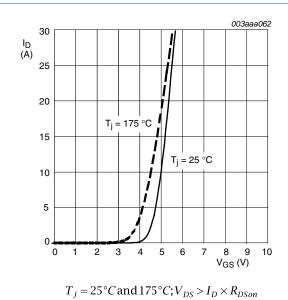
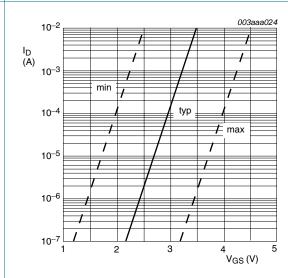


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_i = 25^{\circ}C$

Fig 9. Sub-threshold drain current as a function of gate-source voltage

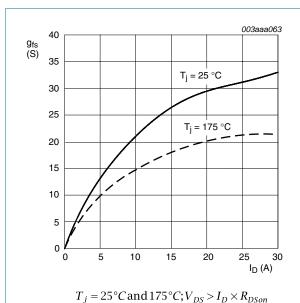


Fig 10. Forward transconductance as a function of drain current; typical values

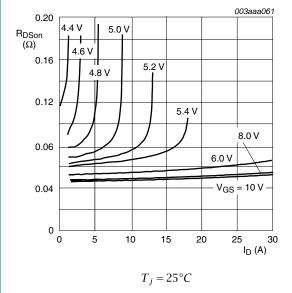
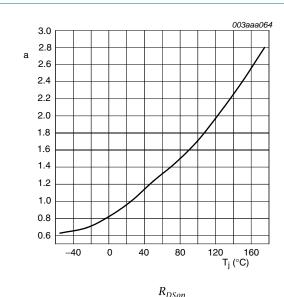
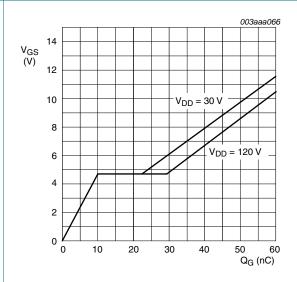


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



factor as a function of junction temperature

 $a = \frac{1}{R_{DSon(25^{\circ}C)}}$ Fig 12. Normalized drain-source on-state resistance



 $I_D = 30A; V_{DS} = 30V \text{ and } 120V$

Fig 13. Gate-source voltage as a function of gate charge; typical values

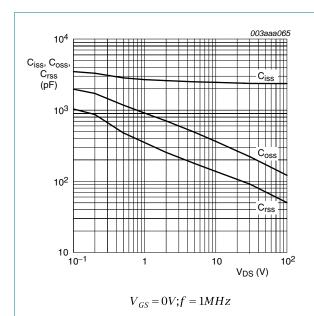


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

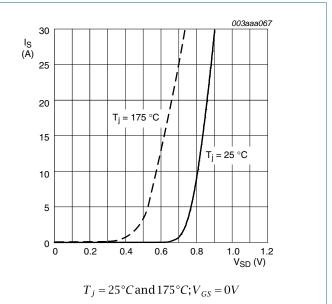
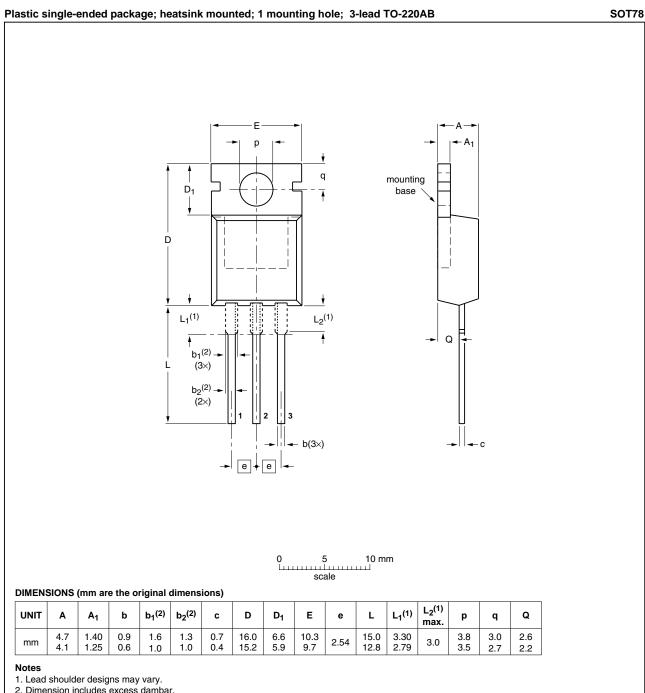


Fig 15. Source current as a function of source-drain voltage; typical values

Package outline



2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP30NQ15T_3	20100303	Product data sheet	-	PHB_PHP30NQ15T-02
Modifications:		of this data sheet has been of NXP Semiconductors.	n redesigned to comply w	ith the new identity
	 Legal texts 	have been adapted to the	new company name whe	re appropriate.
	 Typenumber 	er PHP30NQ15T separated	d from data sheet PHB_PI	HP30NQ15T-02.
PHB_PHP30NQ15T-02 (9397 750 08037)	20010312	Product specification	-	PHB_PHP30NQ15T_1
PHB_PHP30NQ15T_1	19990801	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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